

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S34 1	9850	(metal adj oxide adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 20:59
S34 2	11609	(metal adj oxide adj layer) or (metal adj nitride adj layer) or (metal adj carbide adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:00
S34 3	11609	((metal adj oxide adj layer) or (metal adj nitride adj layer) or (metal adj carbide adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:00
S34 4	1196	((metal adj oxide adj layer) or (metal adj nitride adj layer) or (metal adj carbide adj layer)) and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:00
S34 5	254	((metal adj oxide adj layer) or (metal adj nitride adj layer) or (metal adj carbide adj layer)) with (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:00
S34 6	7	((metal adj oxide adj layer) or (metal adj nitride adj layer) or (metal adj carbide adj layer)) with (gate adj electrode) same (thin near film near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:02
S34 7	4	((metal adj oxide adj layer) or (metal adj nitride adj layer) or (metal adj carbide adj layer)) with (gate adj electrode) same (thin near film near transistor) and (sputter or sputtering or sputtered)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:09
S34 8	7	((metal adj oxide adj layer) or (metal adj nitride adj layer) or (metal adj carbide adj layer)) with (gate) same (thin near film near transistor) and (sputter or sputtering or sputtered)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:09
S34 9	92	((metal adj oxide) or (metal adj nitride) or (metal adj carbide)) with (gate) same (thin near film near transistor) and (sputter or sputtering or sputtered)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:10

## EAST Search History

S35 0	99135	(tft or (thin near film near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:11
S35 1	55919	(tft or (thin near film near transistor)) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:11
S35 2	6234	(tft or (thin near film near transistor)) and gate and (ldd or (lightly adj doped))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:11
S35 3	4028	(tft or (thin near film near transistor)) and gate and (ldd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:11
S35 4	3495	(tft or (thin near film near transistor)) and gate and (ldd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) and (gate adj (insulating or dielectric or oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:11
S35 5	3343	(tft or (thin near film near transistor)) and gate and (ldd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) and (gate adj (insulating or dielectric or oxide)) and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:12
S35 6	3334	(tft or (thin near film near transistor)) and gate and (ldd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) and (gate adj (insulating or dielectric or oxide)) and channel and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:12
S35 7	3057	(tft or (thin near film near transistor)) same gate and (ldd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) and (gate adj (insulating or dielectric or oxide)) and channel and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:12

## EAST Search History

S35 8	2162	(tft or (thin near film near transistor)) same gate same (idd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) and (gate adj (insulating or dielectric or oxide)) and channel and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:12
S35 9	1614	(tft or (thin near film near transistor)) same gate same (idd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) same (gate adj (insulating or dielectric or oxide)) and channel and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:12
S36 0	996	(tft or (thin near film near transistor)) same gate same (idd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) same (gate adj (insulating or dielectric or oxide)) same channel and (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:12
S36 1	846	(tft or (thin near film near transistor)) same gate same (idd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) same (gate adj (insulating or dielectric or oxide)) same channel same (source or drain or source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:13
S36 2	791	(tft or (thin near film near transistor)) same gate same (idd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) same (gate adj (insulating or dielectric or oxide)) same channel same (source or drain or source/drain) and (gate near5 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:13

## EAST Search History

S36 3	334	(tft or (thin near film near transistor)) same gate same (ldd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) same (gate adj (insulating or dielectric or oxide)) same channel same (source or drain or source/drain) and ((gate near5 (multilayer or plurality or multi-layer or first or secod or upper or lower or top or bottom) near layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:14
S36 4	142	(tft or (thin near film near transistor)) same gate same (ldd or (lightly adj doped)) and ((polysilicon or semiconductor) adj layer) same (gate adj (insulating or dielectric or oxide)) same channel same (source or drain or source/drain) and ((gate near5 (multilayer or plurality or multi-layer or first or secod or upper or lower or top or bottom) near layer)) same (oxide or nitride or carbide or oxidize or oxidizing or oxidized or oxidization)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/15 21:15